SPICE Device Model Si3483CDV



Vishay Siliconix

P-Channel 20 V (D-S) MOSFET

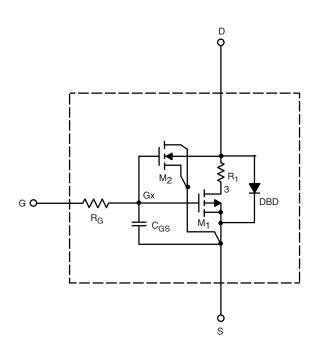
DESCRIPTION

The attached SPICE model describes the typical electrical characteristics of the p-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to + 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage. A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

SUBCIRCUIT MODEL SCHEMATIC

CHARACTERISTICS

- P-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the 55 °C to + 125 °C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics



Note

 This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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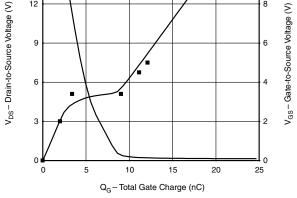
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -250 \ \mu A$	2.1	-	V
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = -10 \text{ V}, \text{ I}_{D} = -6.1 \text{ A}$	0.026	0.027	Ω
		$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -2 \text{ A}$	0.043	0.044	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 15 V, I _D = - 6.1 A	13	13	S
Diode Forward Voltage	V _{SD}	I _S = - 4.9 A	- 0.80	- 0.80	V
Dynamic ^b					
Input Capacitance	C _{iss}	V _{DS} = - 15 V, V _{GS} = 0 V, f = 1 MHz	1030	1000	pF
Output Capacitance	C _{oss}		175	170	
Reverse Transfer Capacitance	C _{rss}		134	140	
Total Gate Charge	0	V_{DS} = - 15 V, V_{GS} = - 10 V, I_D = - 6.1 A	20	22	nC
	Qg		10.70	11.5	
Gate-Source Charge	Q _{gs}	$V_{DS} = -15 V$, $V_{GS} = -4.5 V$, $I_D = -6.1 A$	3.4	3.4	
Gate-Drain Charge	Q _{gd}] [5.7	5.7	

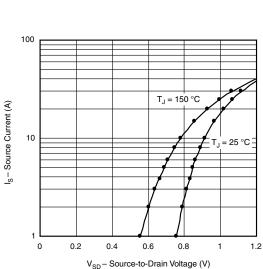
Notes

a. Pulse test; pulse width $\leq 300~\mu\text{s},$ duty cycle $\leq 2~\%.$

b. Guaranteed by design, not subject to production testing.

SHAY www.vishay.com Vishay Siliconix COMPARISON OF MODEL WITH MEASURED DATA (T_J = 25 °C, unless otherwise noted) 5 25 V_{GS} : 10, 7, 6, 5 V 20 4 T_C = 125 °C I_D- Drain Current (A) I_D – Drain Current (A) 15 3 $V_{GS} = 4 V$ - 55 °C 10 2 5 1 $V_{GS} = 3 V$ 25 °C 0 C 2.5 3.0 0.0 0.5 1.0 1.5 2.0 0 1 2 3 4 V_{DS} - Drain-to-Source Voltage (V) V_{GS} - Gate-to-Source Voltage (V) 0.10 1800 ļ 1500 0.08 $R_{DS(on)}$ – On-Resistance (Ω) C_{iss} C – Capacitance (pF) 1200 0.06 V_{GS} = 4.5 V 900 0.04 600 $V_{GS} = 10 V$ Coss 0.02 300 C_{rss} 0.00 0 0 5 15 20 25 0 5 25 10 10 20 30 15 I_D - Drain Current (A) V_{DS} - Drain-to-Source Voltage (V) 100 15 10 V_{DS} V_{GS} 12 8 T_J = 150 °C





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Note

• Dots and squares represent measured data.

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